

1. Scope :

This specification applies to silicon switching diode chips,
Device No. SD-0013C.

2. Structure :

- 2-1. Mesa type.
- 2-2. Electrodes:
P (Anode) Side: Aluminum alloy or gold alloy.
N (Cathode) Side: Gold alloy.

3. Size :

- 3-1. Chip size: 13 mils x 13 mils (0.330 mm x 0.330 mm).
- 3-2. Chip Thickness: 7.5 mils ± 1.5 mils (0.191 mm ± 0.038 mm).
- 3-3. Pattern drawing: Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F =100mA E _e =0mW/cm ²			0.97	V
Reverse Current	I _R	V _R =100V E _e =0mW/cm ²			100	nA
Reverse Breakdown Voltage	V _{(BV)R}	I _R =5μA E _e =0mW/cm ²	100			V

PATTERN DRAWING
UNIT: mil

